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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Moriceau, et al.

Appln. No.: 10/565,621

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PRODUCTION METHOD THEREOF

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FOURTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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This application claims priority to the following patent applications: PCT Application Serial No. PCT/FR04/01858 filed July 15, 2004, which claims the benefit of French patent application No.0308865, filed July 21, 2003. In accordance with 37 C.F.R §1.98(d), the Examiner is directed to the references cited in all Information Disclosure Statements filed in the priority United States patent applications cited above, in addition to the references cited herein.

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Office Action (Non-Final) for Appln. Serial No. 10/474,984 – Dated 09/24/04 (16)
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<p>U.S. District Court District of Delaware (Wilmington) Civil Docket For Case #: 1:08-cv-00292-SLR – (54 pgs)</p>
<p>COMPLAINT filed with Jury Demand against MEMC Electronic Materials Inc. - Magistrate Consent Notice to Pltf. (Filing fee \$ 350, receipt number 152004.) - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Exhibit 1, # 2 Exhibit 2, # 3 Exhibit 3, # 4 Civil Cover Sheet, # 5 Acknowledgement of Consent Form) (sns,) (Entered: 05/20/2008) (47 pgs)</p>
<p>Notice of Availability of a U.S. Magistrate Judge to Exercise Jurisdiction (sns,) (Entered: 05/20/2008) (1 pg)</p>
<p>Report to the Commissioner of Patents and Trademarks for Patent/Trademark Number(s) RE39,484 E; 6,809,009; 7,067,396 B2; (sns,) (Entered: 05/20/2008) (1 pg)</p>
<p>SUMMONS Returned Executed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. MEMC Electronic Materials Inc. served on 5/19/2008, answer due 6/9/2008. (Kraft, Denise) (Entered: 05/20/2008) (2 pgs)</p>
<p>MOTION for Pro Hac Vice Appearance of Attorney George W. Neuner, Alan M. Spiro, Brian M. Gaff and Carolyn D'Agincourt - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Compliance Certification by Counsel To Be Admitted Pro Hac Vice, # 2 Certificate of Compliance Certification by Counsel To Be Admitted Pro Hac Vice, # 3 Certificate of Compliance Certification by Counsel To Be Admitted Pro Hac Vice, # 4 Certificate of Compliance Certification by Counsel To Be Admitted Pro Hac Vice, # 5 Certificate of Service)(Kraft, Denise) (Entered: 05/23/2008) (6 pgs).</p>
<p>STIPULATION TO EXTEND TIME Answer to Complaint to 7/9/08 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 06/05/2008) (1 pg).</p>
<p>MOTION for Pro Hac Vice Appearance of Attorney Robert M. Evans, Jr., David W. Harlan, Richard L. Brophy, Marc W. Vander Tuig - filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Certification of Robert M. Evans, Jr., # 2 Certification of David W. Harlan, # 3 Certification of Richard L. Brophy, # 4 Certification of Marc W. Vander Tuig)(Rogowski, Patricia) (Entered: 06/09/2008) (6 pgs)</p>
<p>MOTION for Pro Hac Vice Appearance of Attorney Michael L. Brody, Richard P. Gilly, Gail J. Standish, Marcus T. Hall and Jason S. Charkow - filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certification By Counsel to be Admitted Pro Hac Vice, # 2 Certification By Counsel to be Admitted Pro Hac Vice, # 3 Certification By Counsel to be Admitted Pro Hac Vice, # 4 Certification By Counsel to be Admitted Pro Hac Vice, # 5 Certification By Counsel to be Admitted Pro Hac Vice)(Kraft, Denise) (Entered: 06/10/2008) (8 pgs)</p>
<p>Disclosure Statement pursuant to Rule 7.1 filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/16/2008) (3 pgs)</p>
<p>MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement - filed by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 07/09/2008) (4 pgs)</p>

OPENING BRIEF in Support re 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 7/28/2008. (Rogowski, Patricia) (Entered: 07/09/2008) (15 pgs)
Disclosure Statement pursuant to Rule 7.1 filed by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 07/09/2008) (3 pgs)
ANSWERING BRIEF in Opposition re 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by Commissariat a L'Energie Atomique. Reply Brief due date per Local Rules is 8/7/2008. (Attachments: # 6 Exhibit A, # 7 Exhibit B, # Certificate of Service) (Kraft, Denise) (Modified on 7/29/2008 (lid). (Entered: 07/28/2008) (29 pgs)
SEALED REPLY BRIEF re 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 08/07/2008) REDACTED REPLY BRIEF re 14 - re 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by MEMC Electronic Materials Inc. (Attachments: # 1 Exhibit 2, # 2 Exhibit 3, # 3 Exhibit 4, # 4 Exhibit 5, # 5 Unreported Cases, # 6 Certificate of Service) (Rogowski, Patricia) Modified on 8/8/2008 (lid). (Entered: 08/07/2008) (98 pgs)
REDACTED REPLY BRIEF re 14 - re 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by MEMC Electronic Materials Inc. (Attachments: # 1 Exhibit 2, # 2 Exhibit 3, # 3 Exhibit 4, # 4 Exhibit 5, # 5 Unreported Cases, # 6 Certificate of Service) (Rogowski, Patricia) Modified on 8/8/2008 (lid). (Entered: 08/07/2008) (98 pgs)
MEMORANDUM ORDER denying 10 MOTION to Dismiss Based upon or, in the Alternative, Motion for a More Definite Statement filed by MEMC Electronic Materials Inc., ORDER, Setting Hearings Telephonic Scheduling Conference set for 3/12/2009 at 9:00 A.M. Signed by Judge Sue L. Robinson on 2/20/2009. (nmf) (Entered: 02/20/2009) (6 pgs)
MOTION for Pro Hac Vice Appearance of Attorney B. Scott Eidson - filed by MEMC Electronic Materials Inc. (Attachments: # 1 Exhibit Certification by Counsel to be Admitted Pro Hac Vice)(Rogowski, Patricia) (Entered: 02/23/2009) (4 pgs)
NOTICE OF SERVICE of Plaintiffs' Initial Disclosures Pursuant to Fed. R. Civ. P. 26(a)(1) by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service) (Kraft, Denise) (Entered: 02/27/2009) (4 pgs)
ANSWER to 1 Complaint, with Jury Trial Demanded, COUNTERCLAIM against all plaintiffs by MEMC Electronic Materials Inc.. (Attachments: # 1 Exhibit A)(Rogowski, Patricia) (Entered: 03/06/2009) (55 pgs)
NOTICE OF SERVICE of MEMC Electronic Materials, Inc.'s Initial Disclosures by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 03/06/2009) (3 pgs)
PROPOSED ORDER Proposed Scheduling Order re 16 Memorandum and Order, Set Hearings, by SOITEC Silicon On Insulator Technologies SA, Commissariat a 'LEnergie Atomique. (Kraft, Denise) (Entered: 03/10/2009) (7 pgs)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft, Esq. regarding [Proposed] Scheduling Order - re 21 Proposed Order, 16 Memorandum and Order, Set Hearings,. (Kraft, Denise) (Entered: 03/10/2009) (1 pg)
STIPULATION TO EXTEND TIME to Respond or Otherwise Plead to Defendant's Counterclaim to April 7, 2009 - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 03/11/2009) (2 pgs)

PROPOSED ORDER Revised Scheduling Order re 21 Proposed Order, 16 Memorandum and Order,, Set Hearings, by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Kraft, Denise) (Entered: 03/12/2009) (7 pgs)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Revised Scheduling Order Pursuant to 03/12/09 Telephonic Scheduling Conference - re 24 Proposed Order. (Kraft, Denise) (Entered: 03/12/2009) (1 pg)
SCHEDULING ORDER: Case referred to the Magistrate Judge for the purpose of exploring ADR. Joiner of Parties due by 8/14/2009. Amended Pleadings due by 8/14/2009. Discovery due by 4/23/2010. Discovery Conference set for 6/25/2009 04:30 PM in Courtroom 6B before Judge Sue L. Robinson. Dispositive Motions due by 6/25/2010. Answering Brief due 7/16/2010. Reply Brief due 7/30/2010. Oral Argument set for 8/27/2010 09:30 AM in Courtroom 6B before Judge Sue L. Robinson. Claim Construction Opening Briefs due by 6/18/2010. Response Briefs due 7/9/2010. Final Pretrial Conference set for 10/14/2010 04:30 PM in Courtroom 6B before Judge Sue L. Robinson. Jury Trial set for 10/25/2010 09:30 AM in Courtroom 6B before Judge Sue L. Robinson. Signed by Judge Sue L. Robinson on 3/16/2009. (nmf) (Entered: 03/16/2009) (7 pgs)
Order Setting Teleconference: Telephone Conference set for 3/23/2009 at 11:00 AM before Judge Mary Pat Thyng to discuss ADR. Signed by Judge Mary Pat Thyng on 3/16/2009. (cak) (Entered: 03/16/2009) (4 pgs)
Order Setting Teleconference: a teleconference has been scheduled for Monday, June 1, 2009 at 10:00 a.m. with Magistrate Judge Thyng to discuss the status of the case and the parties negotiations. Counsel for MEMC shall initiate the teleconference call to 302-573-6173. IT IS FURTHER ORDERED that the Court is holding September 10, September 14 and September 15, 2009 as possible mediation dates. Counsel are to advise Judge Thyng by March 30, 2009 if any of these dates works for everyone to schedule the mediation. Signed by Judge Mary Pat Thyng on 3/23/2009. (cak) (Entered: 03/23/2009) (2 pgs)
ORDER Setting Mediation Conferences: Mediation Conference TENTATIVELY set for 9/15/2009 at 10:00 AM in Courtroom 2B before Judge Mary Pat Thyng. See order for details. Signed by Judge Mary Pat Thyng on 3/24/2009. (cak) (Entered: 03/24/2009) (6 pgs)
MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Text of Proposed Order, # 2 Certificate of Service)(Kraft, Denise) (Entered: 04/07/2009) (5 pgs)
OPENING BRIEF in Support re 30 MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique Answering Brief/Response due date per Local Rules is 4/27/2009. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 04/07/2009) (13 pgs)
ANSWER to 19 Answer to Complaint, Counterclaim Partial Answer to Defendant's Counterclaims, Affirmative Defenses and Soitec Counterclaims, COUNTERCLAIM against MEMC Electronic Materials Inc. by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 04/07/2009) (18 pgs)

NOTICE OF SERVICE of First Request for Production of Documents and Things Directed to Commissariat A L'Energie Atomique; First Request for Production of Documents and Things Directed to SOITEC Silicon on Insulator Technologies, S.A. and Soitec USA, Inc.; and First Set of Interrogatories Directed to SOITEC Silicon on Insulator Technologies, S.A., Soitec USA, Inc. and Commissariat A L'Energie Atomique by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 04/14/2009) (3 pgs)
STIPULATION TO EXTEND TIME Defendant to File Answering Brief in Opposition to Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII to May 6, 2009 - filed by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 04/21/2009) (3 pgs)
ANSWER to 32 Answer to Counterclaim,,, of S.O.I. TEC Silicon on Insulator Technologies, S.A. and SOITEC U.S.A., Inc. by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 04/23/2009) (4 pgs)
STIPULATION TO EXTEND TIME Answering Brief in Opposition to Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V and VIII to May 15, 2009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/06/2009) (3 pgs)
NOTICE OF SERVICE of Soitec's First Set of Interrogatories (Nos. 1-17) and Soitec's First Set of Requests for Production of Documents and Things (Nos. 1-132) by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 05/06/2009) (2 pgs)
STIPULATION TO EXTEND TIME for Defendant to File an Answering Brief in Opposition to Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII; and STIPULATION TO EXTEND TIME for Plaintiffs to File Responses to MEMC's First Requests For Production of Documents and to MEMC's First Set of Interrogatories to May 29, 2009 - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 05/13/2009)
NOTICE of Service of (1) Subpoena to Hayes Soloway, P.C., (2) Subpoena to Pearne & Gordon, LLP, (3) Subpoena to Brinks Hofer Gilson & Lione, and (4) Subpoena to Winston & Strawn by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 05/14/2009) SO ORDERED- re 38 STIPULATION TO EXTEND TIME. Set Briefing Schedule: re 30 MOTION to Dismiss. (Answering Brief due 5/29/2009.) (REFER TO STIPULATION FOR FURTHER DETAILS.). Signed by Judge Sue L. Robinson on 5/15/2009. (lid) (Entered: 05/15/2009)
STIPULATION To Extend Time for Defendant to File Its Answering Brief until June 5, 2009 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/28/2009) SO ORDERED, re 40 Stipulation, Set Briefing Schedule: re 30 MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution. (Answering Brief due 6/5/2009.). Signed by Judge Sue L. Robinson on 5/29/2009. (nmf) (Entered: 05/29/2009)
NOTICE OF SERVICE of (1) Soitec's Objections and Responses to MEMC's First Set of Interrogatories; (2) Soitecs Objections and Responses to MEMC's First Request For Production of Documents and Things; (3) CEAs Objections and Responses to MEMC's First Set of Interrogatories; and (4) CEAs Objections and Responses to MEMC's First Request For Production of Documents and Things by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # 1 Certificate of Service) (Kraft, Denise) (Entered: 05/29/2009)
STIPULATION To extend date to June 19, 2009 by which defendant may file an answering brief in opposition to plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 06/05/2009)

NOTICE OF SERVICE of MEMC's Answers to SOITEC's First Set of Interrogatories (Nos. 1-17) and MEMC's Responses to SOITEC's First Set of Requests for Production of Documents and Things (Nos. 1-132) by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/05/2009)
SO ORDERED- re <u>42</u> Stipulation to Extend Time. Set Briefing Schedule: re <u>30</u> MOTION to Dismiss. (Answering Brief due 6/19/2009.). Signed by Judge Sue L. Robinson on 6/8/2009. (lid) (Entered: 06/08/2009)
NOTICE OF SERVICE of Soitec's Second Set of Requests For Production of Documents and Things (Nos. 133-135) re <u>41</u> Notice of Service,, by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>41</u> Notice of Service,, filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/11/2009)
Letter to Honorable Sue L. Robinson from Patricia Smink Rogowski regarding Transmitting Form of Protective Order. (Attachments: # <u>1</u> Form of Protective Order, # <u>2</u> Exhibit Exhibit A to Form of Protective Order)(Rogowski, Patricia) (Entered: 06/16/2009)
NOTICE OF SERVICE of MEMC's Second Request for Production of Documents and Things Directed to S.O.I.TEC Silicon on Insulator Technologies, S.A. and Soitec USA, Inc. by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 06/16/2009) Set/Reset Hearings: Discovery Conference re-set per joint request of counsel for 9/16/2009 08:30 AM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 06/18/2009)
STIPULATION TO EXTEND TIME Defendant's Answering Brief in Opposition to Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII to July 2, 2009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 06/19/2009) SO ORDERED- re <u>47</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: re <u>30</u> MOTION to Dismiss (Answering Brief due 7/2/2009.). Signed by Judge Sue L. Robinson on 6/23/2009. (lid) (Entered: 06/23/2009) SO ORDERED, re <u>45</u> Protective Order. Signed by Judge Sue L. Robinson on 6/30/2009. (nmf) (Entered: 06/30/2009)
NOTICE of by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique re <u>30</u> MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution <i>Notice of Withdrawal of Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII</i> (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2009)
NOTICE OF SERVICE of MEMC's Responses to SOITEC's Second Set of Requests for Production of Documents and Things Directed to MEMC by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 07/14/2009)
STIPULATION and [Proposed] Order to File an Amended Complaint by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)
NOTICE OF SERVICE of Soitec's Objections and Responses to MEMC's Second Request For Production of Documents and Things Directed To Soitec re <u>46</u> Notice of Service by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>46</u> Notice of Service filed by MEMC Electronic Materials Inc. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)
NOTICE of Withdrawal of Docket Entry 51 by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique re <u>51</u> Notice of Service, (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/17/2009)

NOTICE OF SERVICE of SOITEC's Objections and Responses to MEMC's Second Request for Production of Documents and Things Directed to SOITEC re <u>46</u> Notice of Service by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>46</u> Notice of Service filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/17/2009)
NOTICE OF SERVICE of MEMC Electronic Materials, Inc.'s Second Set of Interrogatories Directed to S.O.I.TEC Silicon on Insulator Technologies, S.A., SOITEC USA, Inc. and Commissariat A L'Energie Atomique by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 07/17/2009)
NOTICE OF SERVICE of Soitec's Production of Documents Bates Numbered SCEA 00000001 to SCEA 00002442 by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/17/2009) SO ORDERED, re <u>50</u> Stipulation. Signed by Judge Sue L. Robinson on 7/20/2009. (nmf) (Entered: 07/20/2009)
NOTICE OF SERVICE of MEMC's Production of Documents Bates Numbered MEMC0300000 to MEMC0306530 by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 07/20/2009)
First AMENDED COMPLAINT for <i>Patent Infringement</i> against MEMC Electronic Materials Inc. - filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit Exhibit 1, # <u>2</u> Exhibit Exhibit 2, # <u>3</u> Exhibit Exhibit 3, # <u>4</u> Exhibit Exhibit 4, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 07/21/2009)
NOTICE OF SERVICE of Soitec S.A.'s Second Set of Interrogatories (Nos. 18-22) and CEA's First Set of Interrogatories (Nos. 1-11) by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/23/2009)
NOTICE OF SERVICE of S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. and COMMISSARIAT A LENERGIE ATOMIQUE SUPPLEMENTAL PRODUCTION OF DOCUMENTS BATES NUMBERED SLIT 00000001 TO SLIT 00049728 re <u>43</u> Notice of Service, by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>43</u> Notice of Service, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/27/2009)
ANSWER to Amended Complaint ANSWER to <u>57</u> Amended Complaint, with Under Federal Rule of Civil Procedure 38, MEMC demands a trial by jury on all issues so triable., COUNTERCLAIM against all plaintiffs by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2009)
NOTICE OF SERVICE of MEMC's Production of Documents Bates Numbered MEMC0300000 - MEMC0337055 by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 08/05/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L Energie Atomique's Revised Supplemental Production of Documents Bates Numbered SLIT00000001 - SLIT0004886; SLIT00004931 SLIT00004985; SLIT00005169 SLIT00005174; SLIT00005241 SLIT00006368; and SLIT00006886 - SLIT00049728 re <u>59</u> Notice of Service, by SOITEC U.S.A., Inc., SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique. Related document: <u>59</u> Notice of Service, filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2009)

STIPULATION TO EXTEND TIME to Answer or Otherwise Respond to MEMC's Amended Counterclaims to August 31, 2009 - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/25/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered SOIT 00000001 to SOIT 00003528 and SLIT 00049729 to SLIT 00060612 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/25/2009)
NOTICE OF SERVICE of MEMC's Production of Documents Bates Numbered MEMC0337056 to MEMC0337503 and MEMC0337504-MEMC0338047 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 08/26/2009)
NOTICE OF SERVICE of (1) SOITECs Supplemental Responses to MEMC Electronic Materials, Inc's First Set of Interrogatories; and (2) CEAs Supplemental Responses to MEMC Electronic Materials, Inc.s First Set of Interrogatories re <u>41</u> Notice of Service,, by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. Related document: <u>41</u> Notice of Service,, filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/26/2009)
NOTICE OF SERVICE of MEMC's Supplemental Answers to SOITEC's First Set of Interrogatories by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 08/27/2009)
SO ORDERED- re <u>63</u> STIPULATION TO EXTEND TIME. Set/Reset Answer Deadlines: SOITEC Silicon On Insulator Technologies SA answer due 8/31/2009; Commissariat a L'Energie Atomique answer due 8/31/2009; SOITEC U.S.A., Inc. answer due 8/31/2009. Signed by Judge Sue L. Robinson on 8/27/2009. (lid) (Entered: 08/27/2009)
ANSWER to <u>60</u> Answer to Amended Complaint, Counterclaim,,, COUNTERCLAIM Reply to Defendant's Amended Counterclaims, Counterclaims And Affirmative Defenses against MEMC Electronic Materials Inc. by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/31/2009)
NOTICE OF SERVICE of MEMC's THIRD SET OF INTERROGATORIES DIRECTED TO S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A., SOITEC USA, INC., AND COMMISSARIAT A L'ENERGIE ATOMIQUE by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 09/01/2009)
ANSWER to <u>68</u> Answer to Counterclaim,,, by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/14/2009). Minute Entry for proceedings held before Judge Sue L. Robinson - Discovery Conference held on 9/16/2009. (Court Reporter V. Gunning.) (nmf) (Entered: 09/16/2009)
NOTICE OF SERVICE of Soitec S.A.'s Third Set of Interrogatories (Nos. 23-27) re <u>58</u> Notice of Service, by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. Related document: <u>58</u> Notice of Service, filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/22/2009)

NOTICE OF SERVICE of MEMC ELECTRONIC MATERIALS INC.'S ANSWERS TO SOITEC S.A.'S SECOND SET OF INTERROGATORIES (NOS. 8-22) and MEMC ELECTRONIC MATERIALS, INC.'S ANSWERS TO CEA'S FIRST SET OF INTERROGATORIES (NOS. 1-11) by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 10/16/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered SOIT 00003529 to SOIT 00004244 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/16/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered SOIT 00003258.001-.057; SOIT 00003342.001-.007; SOIT 00003343.001-.009; (Con't) - SOIT 00003409.001-.015; and SOIT 00003469.001-.015 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/16/2009)
NOTICE OF SERVICE of SOITEC/CEA Parties' Objections and Responses to MEMC Electronic Materials, Inc.'s Second Set of Interrogatories by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/16/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat L'Energie Atomique Supplemental Production of Documents Bates Numbered SOIT 00004245 to SOIT 00205027 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Additional attachment(s) added on 10/23/2009: # <u>2</u> revised) (lid). Modified on 10/23/2009 (lid). (Entered: 10/16/2009)
MOTION to Bifurcate <i>the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order</i> - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/20/2009).
CORRECTING ENTRY: Docket clerk deleted D.I. 78 (opening brief) due to document being filed improperly. Counsel is advised to re-file document using the OPENING BRIEF event code rather than the combined opening and answering brief event code. (lid) (Entered: 10/21/2009)
OPENING BRIEF in Support re <u>77</u> MOTION to Bifurcate <i>the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order</i> filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 11/9/2009. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C)(Rogowski, Patricia) (Entered: 10/21/2009)
NOTICE OF SERVICE of MEMC's PRODUCTION OF DOCUMENTS BATES NUMBERED MEMC0338048-MEMC0345027 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 10/23/2009)

<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique Supplemental Production of Replacement Documents Bates Numbered SCEA 00001337 TO SCEA 00001339; SCEA 00002434 TO SCEA 00002439; SOIT 00007961; SOIT 00006718 TO SOIT 00006727; and SOIT 00007595 TO SOIT 00007598 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/23/2009)</p> <p>CORRECTING ENTRY: Pursuant to request of counsel, correct pdf of D.I. 76 has been attached and text of entry has been modified to correct bates number (lid) (Entered: 10/23/2009)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production Of Documents Bates Numbered SOIT 00205028 to SOIT 00206175; SCEA 00002443 to SCEA 00003974; and SLIT 00060613 to SLIT 00063784 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/28/2009)</p>
<p>NOTICE OF SERVICE of MEMC'S ANSWERS TOSOITEC S.A.'S THIRD SET OF INTERROGATORIES (NOS. 23-27) by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 10/28/2009)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production Of Documents Bates Numbered SOIT 00206176 to SOIT 00206183 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/28/2009)</p>
<p>NOTICE OF SERVICE of SOITEC/CEA Parties' Objections and Responses to MEMC Electronic Materials, Inc.'s Third Set of Interrogatories by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/29/2009)</p>
<p>Cross MOTION to Bifurcate <i>all Collateral Issues</i> - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)</p>
<p>ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate <i>all Collateral Issues</i>, <u>77</u> MOTION to Bifurcate <i>the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order</i> filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Reply Brief due date per Local Rules is 11/20/2009. (Attachments: # <u>1</u> Exhibit, # <u>2</u> Exhibit, # <u>3</u> Exhibit, # <u>4</u> Exhibit, # <u>5</u> Exhibit, # <u>6</u> Exhibit, # <u>7</u> Exhibit, # <u>8</u> Exhibit, # <u>9</u> Exhibit, # <u>10</u> Exhibit, # <u>11</u> Exhibit, # <u>12</u> Declaration, # <u>13</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)</p>
<p>NOTICE OF SERVICE of CEA's Second Set of Interrogatories (Nos. 12-16) by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/11/2009)</p>
<p>CORRECTING ENTRY: Pursuant to request of counsel, Exhibit A to D.I. 86 has been deleted and will be re-filed under seal by counsel at a later time (lid) (Entered: 11/12/2009)</p>
<p>SEALED EXHIBIT re <u>86</u> Answering Brief in Opposition,, by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/12/2009)</p>

<p>REPLY BRIEF re <u>77</u> MOTION to Bifurcate <i>the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order</i> filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3)(Rogowski, Patricia) (Entered: 11/17/2009)</p>
<p>ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate <i>all Collateral Issues</i> filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 12/3/2009. (Rogowski, Patricia) (Entered: 11/19/2009)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered SOIT 00206184 to SOIT 00206997 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2009)</p>
<p>NOTICE OF SERVICE of (1) Subpoena in a Civil Case to J. William Dockrey; (2) Subpoena in a Civil Case to Allan Fanucci, Esq.; (3) Amended Notice of Videotaped Deposition of Saeed Pirooz; (4) Notice of Videotaped Deposition of Commissariat a L'Energie Atomique; and (5) Notice of Videotaped Deposition of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Soitec U.S.A., Inc. by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 11/30/2009)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered BHRO00000001 to BHRO00036157 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/02/2009)</p>
<p>REPLY BRIEF re <u>85</u> Cross MOTION to Bifurcate <i>all Collateral Issues</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit Declaration of Marcus T. Hall in Support of Plaintiffs' Reply Re: Cross-Motion to Bifurcate all Collateral Issues)(Kraft, Denise) (Entered: 12/03/2009)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production of Three Boxes of Wafer Samples by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/08/2009). Set Hearings: Discovery Conference set for 12/21/2009 04:00 PM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 12/09/2009).</p>
<p>NOTICE OF SERVICE of (1) SIX CARTONS OF 300 MM WAFER SAMPLES AND 1 CARTON OF 200 MM WAFER SAMPLES; (2) DOCUMENTS MARKED MEMC0345028-MEMC0345084; (3) DOCUMENTS MARKED MEMC0345085-MEMC0345133; (4) MEMC'S ANSWERS TO CEA'S SECOND SET OF INTERROGATORIES (NOS. 12-16); AND (5) MEMC'S FIRST SET OF REQUESTS FOR ADMISSION TO S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. AND SOITEC USA, INC. by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 12/14/2009)</p>
<p>MOTION for Leave to File <i>Stipulated Motion for Leave to File a Sur-Reply Brief in Support of MEMC's Motion to Bifurcate</i> - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 12/14/2009)</p>
<p>REDACTED VERSION of <u>88</u> Exhibit to a Document <i>Cross Motion to Bifurcate all Collateral Issues</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/14/2009). SO ORDERED- re <u>97</u> MOTION for Leave to File. Signed by Judge Sue L. Robinson on 12/16/2009. (lid) (Entered: 12/16/2009)</p>

SUR-REPLY BRIEF re 77 MOTION to Bifurcate *the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order* MEMC's SUR-REPLY BRIEF IN SUPPORT OF ITS MOTION TO BIFURCATE THE ISSUES OF WILLFULNESS AND DAMAGES FOR PURPOSES OF DISCOVERY AND TRIAL filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/16/2009)

NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Supplemental Production of Documents Bates Numbered SOIT 00207008 TO SOIT 00207591 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 12/17/2009). Minute Entry for proceedings held before Judge Sue L. Robinson - Conference held on 12/21/2009. (Court Reporter V. Gunning.) (nmf) (Entered: 12/22/2009). ORAL ORDER by Judge Sue L. Robinson in open court on 12/21/2009 granting 77 MOTION to Bifurcate *the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order*, denying 85 Cross MOTION to Bifurcate *all Collateral Issues*. (nmf) (Entered: 12/22/2009).

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Production 12 of CD-ROM Documents Bates Numbered SOIT 00207008 TO SOIT 00207591 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..(Kraft, Denise) (Entered: 12/22/2009)

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Supplemental Production of Documents Bates Numbered BHRO00036158 to BHRO00036584, served on December 11, 2009; and S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Supplemental Production of Documents Bates Numbered BHRO00036585 to BHRO00036731, served on December 18, 2009 by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 12/22/2009). CORRECTING ENTRY: Pursuant to conversation docket clerk deleted Notice of filing due to document being filed improperly. Counsel will re-file document at a later time. (lid) (Entered: 01/04/2010).

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Soitec USA, Inc.'s Objections and Responses to MEMC's November 25, 2009 Notice of 30(b)(6) Deposition of Soitec, and Commissariat a l'Energie Atomique's Objections and Responses to MEMC's November 25, 2009 Notice of 30(b)(6) Deposition of CEA by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 01/04/2010).

STIPULATION To Amend Scheduling Order re 26 Scheduling Order,,, by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/06/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Production of Documents Bates Numbered HS00000001 to HS0000792 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 01/06/2010)

NOTICE OF SERVICE of Documents Marked (1) MEMC0345134-MEMC0391283 and (2) MEMC0391284-MEMC0413109 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/07/2010). SO ORDERED- re 104 Stipulation Amending Scheduling Order. ORDER- Setting Scheduling Order Deadlines (Claims Construction Opening Brief due by 6/18/2010., Discovery due by 6/18/2010.)(REFER TO STIPULATION FOR FURTHER DETAILS). Signed by Judge Sue L. Robinson on 1/7/2010. (lid) (Entered: 01/07/2010).

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Soitec USA, Inc.'s Responses to MEMC Electronic Materials, Inc.'s First Set of Requests for Admission by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/11/2010)
NOTICE OF SERVICE of Documents Marked MEMC0413110-MEMC0459972 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/13/2010)
NOTICE OF SERVICE of Notice of Videotaped Depositions of Emmanuel Huyghe, Clotilde Turleque, Christophe Maleville and Hubert Moriceau by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/14/2010)
NOTICE OF SERVICE of Notice of Videotaped Deposition of Norman Soloway by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/14/2010)
NOTICE OF SERVICE of Notice of Videotaped Depositions of (1) Emmanuel Arene, (2) Bruno Ghyselen, (3) Thierry Barge, (4) Chrystelle Legahe, (5) Konstantine Bourdelle, (6) Andre-Jacques Auberton-Herve, (7) Bernard Aspar, (8) Thierry Poumeyrol, and (9) Michel Bruel by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/20/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Production 16 of CD-ROM Documents Bates Numbered SOIT 00207592 to SOIT 00218102 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/20/2010)
MOTION for Pro Hac Vice Appearance of Attorney Laura K. Carter - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certification, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 01/21/2010). SO ORDERED- re <u>113</u> MOTION for Pro Hac Vice Appearance of Attorney Laura K. Carter. Signed by Judge Sue L. Robinson on 1/26/2010. (lid) (Entered: 01/26/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Production 17 of CD-Rom Documents Bates Numbered SOIT 00218103 to SOIT 00219113 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/27/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat L'Energie Atomique's Production of Documents Bates Numbered SOIT 00219114 to SOIT 00219229 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/27/2010)
NOTICE OF SERVICE of Documents Marked (1) MEMC0459973-MEMC-0526213; (2) MEMC0526214-MEMC-0526273; and (3) MEMC0484547-MEMC0526213 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 01/29/2010)
NOTICE OF SERVICE of Six DVDs Containing Documents Marked MEMC0526274-MEMC0582949 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 02/02/2010)
NOTICE OF SERVICE of Documents Marked MEMC0582950 - MEMC0618792 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 02/08/2010)
NOTICE OF SERVICE of Documents Marked (1) MEMC0618793-MEMC0697890 and (2) MEMC0697891-MEMC0715676 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 02/12/2010)

NOTICE OF SERVICE of Documents Marked MEMC0715677-MEMC0772697 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 02/18/2010)
NOTICE OF SERVICE of Notice of Videotaped Deposition by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 02/19/2010)
NOTICE OF SERVICE of S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. and COMMISSARIAT LENERGIE ATOMIQUES PRODUCTION 19 OF CD-ROM DOCUMENTS BATES NUMBERED SOIT 00219230 - SOIT 00242462, SOIT 00242514 - SOIT 00271070, SOIT 00271093 - SOIT 00277765, SOIT 00277802 - SOIT 00280854 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 03/02/2010)
NOTICE OF SERVICE of S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. and COMMISSARIAT LENERGIE ATOMIQUES PRODUCTION 20 OF CD-ROM DOCUMENTS BATES NUMBERED SOIT 00280855 - SOIT 00310785 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 03/02/2010)
NOTICE OF SERVICE of S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. and COMMISSARIAT LENERGIE ATOMIQUES PRODUCTION 21 OF CD-ROM DOCUMENTS BATES NUMBERED SCEA 00003975 - SCEA 00004146 and SOIT 00310786 - SOIT 00336534 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 03/02/2010)
NOTICE OF SERVICE of S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A. and COMMISSARIAT LENERGIE ATOMIQUES PRODUCTION 22 OF CD-ROM DOCUMENTS BATES NUMBERED SCEA 00004147 - SCEA 00031465 and SOIT 00336535 - SOIT 00355547 and SOIT 00355554 - SOIT 00359693 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 03/02/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Fourth Set of Interrogatories (Nos. 28-29) Directed to MEMC Electronic Materials, Inc. by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Additional attachment(s) added on 3/24/2010: # <u>1</u> Certificate of Service) (fms). (Entered: 03/03/2010)
STIPULATION to Amend Scheduling Order re <u>26</u> Scheduling Order,,, by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 03/12/2010). SO ORDERED- re <u>127</u> Stipulation to Amend Scheduling Order. ORDER- Setting Scheduling Order Deadlines (Claims Construction Opening Brief due by 6/18/2010., Discovery due by 6/18/2010.) (REFER TO STIPULATION FOR DETAILS). Signed by Judge Sue L. Robinson on 3/15/2010. (lid) (Entered: 03/15/2010)

NOTICE OF SERVICE of (1) MEMC Electronic Materials, Inc.'s Second Set of Requests for Admission Directed to Plaintiffs and (2) MEMC Electronic Materials, Inc.'s Fourth Set of Interrogatories Directed to S.O.I.TEC Silicon on Insulator Technologies, S.A., SOITEC USA, Inc. and Commissariat A L'Energie Atomique by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 03/23/2010).

CORRECTING ENTRY: Per request of counsel, the pdf attached to D.I. 126 (NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Fourth Set of Interrogatories (Nos. 28-29) Directed to MEMC Electronic Materials, Inc. by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.) has been deleted and replaced with the proper attachment with the correct date. (fms) (Entered: 03/24/2010).

CORRECTING ENTRY: Per request of counsel, D.I. 129 has been deleted and will be re-filed at a later time. (lid) (Entered: 03/29/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 23 Bates Numbered SOIT 00359694 and SOIT 00359695, including Wafer Samples by SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 03/29/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 24 of CD-ROM Documents Bates Numbered SOIT 00359696 - SOIT 00419315 by SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 04/01/2010)

NOTICE OF SERVICE of Electronic Production of OCR Text Files related to: (1) S.O.I.TEC Silicon on Insulator Technologies, S.A.'s Production 19 Bates Numbered SOIT 00219230 - SOIT 00242462; SOIT 00242514 - SOIT 00271070; SOIT 00271093 - SOIT 00277765; SOIT 00277802 - SOIT 00280854; (2) S.O.I.TEC Silicon on Insulator Technologies, S.A.'s Production 20 Bates Numbered SOIT 00280855 - SOIT 00310785; and (3) S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production 22 Bates Numbered SCEA 00004147 - SCEA 00031465; SOIT 00336535 - SOIT 00355547; and SOIT 00355554 - SOIT 00359693 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 04/07/2010)

NOTICE OF SERVICE of (1) Documents marked MEMC0772698-MEMC0775891; (2) Documents marked CRAV00000001-CRAV00000098; and (3) Document marked MEMC0775892 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 04/07/2010)

NOTICE OF SERVICE of MEMC ELECTRONIC MATERIALS, INC.'S SUPPLEMENTAL ANSWER TO CEA'S FIRST SET OF INTERROGATORIES, MEMC'S ANSWERS TO SOITEC S.A.'S FOURTH SET OF INTERROGATORIES (NOS. 28-29), and MEMC'S SUPPLEMENTAL ANSWERS TO SOITEC S.A.'S THIRD SET OF INTERROGATORIES (NO. 23) by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 04/07/2010). Set Hearings: Discovery Conference set for 4/23/2010 09:30 AM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 04/21/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production of Documents Bates Numbered SOIT 00419316 (updated from previously produced documents Bates numbered SOIT 00000159 - SOIT 00000161) by SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 04/22/2010).

Minute Entry for proceedings held before Judge Sue L. Robinson - Discovery Conference held on 4/23/2010. (Court Reporter V. Gunning.) (nmf) (Entered: 04/23/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's electronic production of: (1) Production #25 Bates Numbered SCEA00031466-SCEA00032999; SOIT00419316-SOIT00422470; and SOIT00422478-SOIT00461551; (2) Production #26 Bates Numbered SCEA00033000-SCEA00165680; SCEA00165686-SCEA00167229; SCEA00167232-SCEA00167288; and SOIT00461552-SOIT00474611; and (3) Production #27 Bates Numbered SCEA00167289-SCEA00167291; and SOIT00474611-SOIT00476375 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 04/29/2010)
NOTICE OF SERVICE of Commissariat a L'Energie Atomique's Production #28 of CD-ROM Documents Bates Numbered SCEA00167292-SCEA00167308 by Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 04/29/2010)
NOTICE OF SERVICE of (1) Notice of Videotaped Deposition (Michael Bruel) and (2) Notice of Videotaped Deposition (S.O.I.TEC Silicon on Insulator Technologies, S.A. and SOITEC USA, Inc.) by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 05/03/2010)
NOTICE OF SERVICE of (1) DVD Containing Video Marked CRA V00000099; (2) CD Containing Documents Marked MEMC0775893-MEMC0775948; (3) CD Containing Documents Marked MEMC0775949-MEMC0775954; and (4) DVD Containing Documents Marked MEMC0775955-MEMC0781961 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 05/03/2010)
NOTICE OF SERVICE of Commissariat a L'Energie Atomique's Production #29 of CD-ROM Documents Bates Numbered SCEA 00167309 - SCEA 00167315 by Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/03/2010)
NOTICE OF SERVICE of (1) S.O.I.TEC Silicon On Insulator Technologies, S.A., SOITEC USA, Inc., and Commissariat a L'Energie Atomique's Responses To MEMC's Fourth Set of Interrogatories; and (2) S.O.I.TEC Silicon On Insulator Technologies, S.A., and Commissariat a L'Energie Atomique's Responses To MEMC's Second Set of Requests for Admissions re <u>128</u> Notice of Service, by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Related document: <u>128</u> Notice of Service, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/04/2010). Reset Hearings: Oral Argument re-set per joint request of counsel for 9/3/2010 09:30 AM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 05/05/2010)
MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/07/2010)
OPENING BRIEF in Support re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 5/24/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6, # <u>7</u> Exhibit 7, # <u>8</u> Exhibit 8, # <u>9</u> Exhibit 9, # <u>10</u> Exhibit 10, # <u>11</u> Exhibit 11, # <u>12</u> Exhibit 12, # <u>13</u> Exhibit 13, # <u>14</u> Exhibit 14, # <u>15</u> Exhibit 15)(Rogowski, Patricia) (Entered: 05/07/2010)

NOTICE OF SERVICE of CD-ROM including re-submittal of documents Bates numbered SOIT 00310798-00336526 as Document Bates numbered SOIT 00310798 in native format by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/20/2010)
NOTICE OF SERVICE of Amended Notices of Videotaped Deposition of (1) Dr. Bernard Aspar and (2) Dr. Michel Bruel by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 05/21/2010)
ANSWERING BRIEF in Opposition re <u>141</u> MOTION for Discovery <i>MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian</i> filed by SOITEC Silicon On Insulator Technologies SA.Reply Brief due date per Local Rules is 6/4/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
DECLARATION re <u>145</u> Answering Brief in Opposition,, <i>Declaration of Marcus T. Hall in Support of Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian</i> by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft, Esq. regarding [Proposed] Third Stipulation to Amend Scheduling Order - re <u>26</u> Scheduling Order,.,,. (Attachments: # <u>1</u> Text of Proposed Order)(Kraft, Denise) (Entered: 05/25/2010). CORRECTING ENTRY: Stipulation attached to D.I. 147 has been deleted due to document being filed improperly. Counsel is advised to re-file document using the STIPULATION event code (lid) (Entered: 05/25/2010).
STIPULATION [Proposed] Third Stipulation to Amend Scheduling Order re <u>26</u> Scheduling Order,,, <u>147</u> Letter by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 05/25/2010). SO ORDERED- re <u>148</u> to Amend Scheduling Order. ORDER- Setting Scheduling Order Deadlines (Claims Construction Opening Brief due by 6/25/2010., Discovery due by 7/30/2010., Dispositive Motions due by 7/2/2010., Answering Brief due 7/16/2010., Reply Brief due 7/30/2010.). Signed by Judge Sue L. Robinson on 5/26/2010. (lid) (Entered: 05/26/2010)
NOTICE OF SERVICE of Expert Reports of (1) Peter Moran, (2) John T. Goolkasian, (3) Robert Averback, and (4) Pascal Bellon by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/02/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 31 of CD-ROM Documents Bates Numbered SOIT 00476382 to SOIT 00476394 by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/02/2010)
NOTICE OF SERVICE of (1) Expert Report of Andrew Hirt; (2) Expert Report of John Bravman regarding Invalidity of United States Patent No. 5,834,812; and (3) Expert Report of John Bravman regarding Infringement by Defendant MEMC by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/02/2010)

<p>REPLY BRIEF IN SUPPORT OF <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6)(Rogowski, Patricia) Modified on 6/4/2010 (lid). (Entered: 06/04/2010)</p>
<p>NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 32 of CD-ROM Documents Bates Numbered SOIT 00476395 to SOIT 00476441 by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/07/2010)</p>
<p>STATEMENT re <u>148</u> Stipulation <i>Joint Claim Construction Statement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)</p>
<p>CLAIM Construction Chart by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)</p>
<p>NOTICE OF SERVICE of (1) S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 33 of CD-ROM Documents Bates Numbered SOIT 00476442 to SOIT 00476456; and (2) S.O.I.TEC Silicon On Insulator Technologies, S.A.'s Production 33 Supplement including CD-ROM Documents Bates Numbered SOIT 00476442 to SOIT 00476456 (duplicates of Production 33) and SOIT 00476457 (Burg Translations, Inc. Certification) by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)</p>
<p>SUR-REPLY BRIEF re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)</p>
<p>DECLARATION re <u>157</u> Sur-Reply Brief, Declaration of Marcus T. Hall in Support of Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)</p>
<p>NOTICE of Service of Videotaped Depositions for Dr. John C. Bravman and Andrew M. Hirt by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 06/18/2010)</p>
<p>STIPULATION Stipulated Motion for Leave to Exceed Page Limit Under Delaware L.R. 7.1.3 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 06/21/2010); SO ORDERED- re <u>160</u> Stipulated Motion for Leave to Exceed Page Limit. Signed by Judge Sue L. Robinson on 6/22/2010. (lid) (Entered: 06/22/2010)</p>
<p>NOTICE OF SERVICE of (1) Rebuttal Expert Report of Robert Averback; (2) Report on Characterization of Si Wafers by Transmission Electron Microscopy (Pascal Bellon); and (3) Rebuttal Expert Report of Peter Moran by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/22/2010)</p>
<p>NOTICE OF SERVICE of Supplemental Expert Report of Peter Moran by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/22/2010)</p>
<p>NOTICE OF SERVICE of Documents Marked MEMC0781986-MEMC0782012 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/23/2010)</p>

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's: (1) Notice of Deposition of Dr. Peter Moran; (2) Notice of Deposition of Dr. Robert Averback; and (3) Notice of Deposition of Dr. Pascal Bellon by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/24/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's List of Fact Witnesses by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/24/2010)
NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's: (1) Supplemental Expert Report of Andrew M. Hirt; and (2) Expert Report of John C. Bravman Regarding Non-infringement of U.S. Patent No. 5,834,812 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/24/2010)
CLAIM CONSTRUCTION OPENING BRIEF filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0001-DA0006, # 2 Appendix DA0007-DA0032, # 3 Appendix DA0033-DA0072, # 4 Appendix DA0073-DA0112, # 5 Appendix DA0113-DA0152, # 6 Appendix DA0153-DA0192, # 7 Appendix DA0193-DA0232, # 8 Appendix DA0233-DA0272, # 9 Appendix DA0273-DA0312, # 10 Appendix DA0313-DA0352, # 11 Appendix DA0353-DA0392, # 12 Appendix DA0393-DA0432, # 13 Appendix DA0433-DA0472, # 14 Appendix DA0473-DA0512, # 15 Appendix DA0513-DA0521, # 16 Appendix DA0522-DA0545, # 17 Appendix SEALED - DA0546-DA0551, # 18 Appendix DA0552-DA0563, # 19 Appendix SEALED - DA0564-DA0566, # 20 Appendix DA0567-DA0573, # 21 Appendix SEALED - DA0574-DA0599, # 22 Appendix DA0600-DA0604, # 23 Appendix DA0605-DA0609, # 24 Appendix DA0610-DA0625, # 25 Appendix DA0626-0634, # 26 Appendix DA0635, # 27 Appendix DA0636-DA0652, # 28 Appendix SEALED - DA0653-DA0657, # 29 Appendix DA0658-DA0667, # 30 Appendix DA0668-DA0670, # 31 Appendix DA0671-DA0678, # 32 Appendix DA0679-DA0687, # 33 Appendix DA0688-DA0696, # 34 Appendix SEALED - DA0697-DA0705, # 35 Appendix SEALED - DA0706-DA0711, # 36 Appendix SEALED - DA0712-DA0714, # 37 Appendix DA0715-DA0717, # 38 Appendix DA0718-DA0719, # 39 Appendix DA0720-DA0722, # 40 Appendix DA0723-DA0732, # 41 Appendix DA0733-DA0740, # 42 Appendix DA0741-DA0749, # 43 Appendix DA0750-DA0769, # 44 Appendix DA0770-DA0781)(Rogowski, Patricia) (Entered: 06/25/2010)
CLAIM CONSTRUCTION OPENING BRIEF <i>Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)
DECLARATION re 168 Claim Construction Opening Brief, <i>Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)
SEALED EXHIBIT re 169 Declaration, <i>Exhibit A (Filed Under Seal) to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

SEALED EXHIBIT re 169 Declaration, *Exhibit B (Filed Under Seal) to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief* by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

SEALED EXHIBIT re 169 Declaration, *Exhibit C (Filed Under Seal) to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief* by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) Vol. I - JA0001 to JA0533; (2) Vol. II - JA0534 to JA0930; (3) Vol. III - JA0931 to JA1502; (4) Vol. IV - JA1503 to JA1510 (Filed Under Seal); (5) Vol. V - JA1511 to JA2089; and (6) Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010); CORRECTING ENTRY: Docket clerk deleted appendices to D.I. 167 due to documents being filed improperly. Counsel is advised to re-file appendices separately using the APPENDIX event code. Counsel is also advised that sealed documents may not be filed with public view documents. (lid) (Entered: 06/28/2010)

(Document too large to file in pdf format, will file at later date by Express Mail).
APPENDIX re 167 Claim Construction Opening Brief,,,,,, by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA-0001 - DA-0006, # 2 Appendix DA-0007 - DA-0032, # 3 Appendix DA-0033 - DA-0072, # 4 Appendix DA-0073 - DA-0112, # 5 Appendix DA-0113 - DA-0152, # 6 Appendix DA-0153 - DA-0192, # 7 Appendix DA-0193 - DA-0232, # 8 Appendix DA-0233 - DA-0272, # 9 Appendix DA-0273 - DA-0312, # 10 Appendix DA-0313 - DA-0352, # 11 Appendix DA-0353 - DA-0392, # 12 Appendix DA-0393 - DA-0432, # 13 Appendix DA-0433 - DA-0472, # 14 Appendix DA-0473 - DA-0512, # 15 Appendix DA-0513 - DA-0521)(Rogowski, Patricia) (Entered: 06/28/2010)

SEALED APPENDIX re 167 Claim Construction Opening Brief,,,,,, by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 06/28/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production 34 of CD-ROM Documents Bates Numbered SOIT 00476458 to SOIT 00476602 by SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/28/2010)

REDACTED VERSION of 175 Appendix by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0522-DA0545, # 2 Appendix DA0546-DA0551, # 3 Appendix DA0552-DA0563, # 4 Appendix DA0564-DA0566, # 5 Appendix DA0567-DA0573, # 6 Appendix DA0574-DA0599, # 7 Appendix DA0600-DA0604, # 8 Appendix DA0605-DA0609, # 9 Appendix DA0610-DA0625, # 10 Appendix DA0626-DA0634, # 11 Appendix DA0635, # 12 Appendix DA0636-DA0652, # 13 Appendix DA0653-DA0657, # 14 Appendix DA0658-DA0667, # 15 Appendix DA0668-DA0670, # 16 Appendix DA0671-DA0678, # 17 Appendix DA0679-DA0687, # 18 Appendix DA0688-DA0696, # 19 Appendix DA0697-DA0705, # 20 Appendix DA0706-DA-0711, # 21 Appendix DA0712-DA0714, # 22 Appendix DA0715-DA0717, # 23 Appendix DA0718-DA0719, # 24 Appendix DA0720-DA0722, # 25 Appendix DA0723-DA0732, # 26 Appendix DA0733-DA0740, # 27 Appendix DA0741-DA0749, # 28 Appendix DA0750-DA0769, # 29 Appendix DA0770-DA0781, # 30 Certificate of Service)(Rogowski, Patricia) (Entered: 06/28/2010)

(Document too large to file in pdf format, will file at later date by Express Mail).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) **Vol. I** - JA0001 to JA0533.

APPENDIX VOL I. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010)

(Document too large to file in pdf format, will file at later date by Express Mail).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (2) **Vol. II** - JA0534 to JA0930.

APPENDIX VOL II. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010)

(Document too large to file in pdf format, will file at later date by Express Mail).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (3) **Vol. III** – JA0931 to JA1502.

APPENDIX VOL III. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).

(Document too large to file in pdf format, will file at later date by Express Mail).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (4) **Vol. IV** – JA1503 to JA1510.

APPENDIX VOL IV. re 173 Notice of Filing Paper Documents, (OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).

(Document too large to file in pdf format, will file at later date by Express Mail).

NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (5) **Vol. V** – JA1511 to JA2089.

(Document too large to file in pdf format, will file at later date by Express Mail). Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010).

SEALED APPENDIX re 168 Claim Construction Opening Brief, *Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI - Filed Under Seal* by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/28/2010)

NOTICE OF SERVICE of S.O.I.TEC Silicon on Insulator Technologies, S.A.'s and Commissariat a L'Energie Atomique's List of Rebuttal Fact Witnesses by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/30/2010)

NOTICE OF SERVICE of Amended Notice of Videotaped Deposition of Dr. John C. Bravman by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 06/30/2010)
MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony</i> - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment of <i>Invalidity of the Asserted Aspar Patent Claims</i> - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>186</u> MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>187</u> MOTION for Partial Summary Judgment of <i>Invalidity of the Asserted Aspar Patent Claims</i> filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Rogowski, Patricia) (Entered: 07/02/2010)
SEALED APPENDIX re <u>189</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Table of Contents, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
(Document too large to file in pdf format, will file at later date by Express Mail). APPENDIX re <u>186</u> MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix Vol. II of XIX, # <u>2</u> Appendix Vol. III of XIX, # <u>3</u> Appendix Vol. IV of XIX, # <u>4</u> Appendix Vol. V of XIX, # <u>5</u> Appendix Vol. VII of XIX, # <u>6</u> Appendix Vol. IX of XIX, # <u>7</u> Appendix Vol. XI of XIX, # <u>8</u> Appendix Vol. XII of XIX, # <u>9</u> Appendix Vol. XIII of XIX, # <u>10</u> Appendix Vol. XIV of XIX, # <u>11</u> Appendix Vol. XV of XIX, # <u>12</u> Appendix Vol. XVI of XIX, # <u>13</u> Appendix Vol. XVIII of XIX, # <u>14</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED APPENDIX re <u>186</u> MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 - Vol. VI of XIX (FILED UNDER SEAL)</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED APPENDIX re <u>186</u> MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 - Vol. VIII of XIX (FILED UNDER SEAL)</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

SEALED APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 - Vol. X of XIX (FILED UNDER SEAL) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 - Vol. XVII of XIX (FILED UNDER SEAL) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 - Vol. XIX of XIX (FILED UNDER SEAL) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
SEALED OPENING BRIEF in Support re <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Summary Judgment of Non-Infringement - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
SEALED OPENING BRIEF in Support re <u>199</u> MOTION for Summary Judgment of Non-Infringement filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
SEALED APPENDIX re <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Table of Contents, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid</i> - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>204</u> MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment <i>SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct</i> - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>206</u> MOTION for Partial Summary Judgment <i>SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents</i> - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>208</u> MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment <i>SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement</i> - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>210</u> MOTION for Partial Summary Judgment <i>SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement</i> filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment <i>SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art</i> - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)

<p>OPENING BRIEF in Support re <u>212</u> MOTION for Partial Summary Judgment SOITEC's <i>Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art</i> filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)</p>
<p>OPENING BRIEF in Support re <u>213</u> MOTION for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> filed by SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)</p>
<p>CORRECTING ENTRY: Per request of counsel, D.I. number 216 has been deleted and will be re-filed at a later time (lid) (Entered: 07/07/2010)</p>
<p>CORRECTING ENTRY: Per request of counsel, D.I. number 217 has been deleted and will be re-filed at a later time (lid) (Entered: 07/07/2010)</p>
<p>REDACTED VERSION of <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010);</p>
<p>CORRECTING ENTRY: Per request of counsel, D.I. numbers 216 and 217 have been deleted and will be re-filed at a later time (lid) (Entered: 07/07/2010)</p>
<p>REDACTED VERSION of <u>201</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0001 - MA0004, # <u>2</u> Appendix MA0005 - MA0010, # <u>3</u> Appendix MA0011 - MA0016, # <u>4</u> Appendix MA0017 - MA0020, # <u>5</u> Appendix MA0021 - MA0029, # <u>6</u> Appendix MA0030 - MA0045, # <u>7</u> Appendix MA0046 - MA0052, # <u>8</u> Appendix MA0053 - MA0078, # <u>9</u> Appendix MA0079 - MA0092, # <u>10</u> Appendix MA0093 - MA0129, # <u>11</u> Appendix MA0130 - MA0148, # <u>12</u> Appendix MA0149 - MA0160, # <u>13</u> Appendix MA0161 - MA0163, # <u>14</u> Appendix MA0164 - MA0167, # <u>15</u> Appendix MA0168 - MA0172, # <u>16</u> Appendix MA0173 - MA0183, # <u>17</u> Appendix MA0184 - MA0196, # <u>18</u> Appendix MA0197 - MA0207, # <u>19</u> Appendix MA0208 - MA0241, # <u>20</u> Appendix MA0242 - MA0245, # <u>21</u> Appendix MA0246 - MA0249, # <u>22</u> Appendix MA0250 - MA0252, # <u>23</u> Appendix MA0253 - MA0265, # <u>24</u> Appendix MA0266 - MA0281, # <u>25</u> Appendix MA0282 - MA0312, # <u>26</u> Appendix MA0313 - MA0359, # <u>27</u> Appendix MA0360 - MA0365, # <u>28</u> Appendix MA0366, # <u>29</u> Appendix MA0367 - MA0400, # <u>30</u> Appendix MA0401 - MA0474, # <u>31</u> Appendix MA0475 - MA0483, # <u>32</u> Certificate)(Rogowski, Patricia) (Entered: 07/07/2010)</p>
<p>REDACTED VERSION of <u>190</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0484 - MA0489, # <u>2</u> Appendix MA0490 - MA0515, # <u>3</u> Appendix MA0516 - MA0534, # <u>4</u> Appendix MA0535 - MA0541, # <u>5</u> Appendix MA0542 - MA0550, # <u>6</u> Appendix MA0551 - MA0561, # <u>7</u> Appendix MA0562 - MA0564, # <u>8</u> Appendix MA0565 - MA0569, # <u>9</u> Appendix MA0570 - MA0574, # <u>10</u> Appendix MA0575 - MA0576, # <u>11</u> Appendix MA0577 - MA0601, # <u>12</u> Appendix MA0602 - MA0603, # <u>13</u> Appendix MA0604 - MA0605, # <u>14</u> Appendix MA0606 - MA0609, # <u>15</u> Appendix MA0610 - MA0612, # <u>16</u> Appendix MA0613 - MA0625, # <u>17</u> Appendix MA0626 - MA0628, # <u>18</u> Appendix MA0629 - MA0630, # <u>19</u> Appendix MA0631 - MA0653, # <u>20</u> Appendix MA0654 - MA0685, # <u>21</u> Appendix MA0686 - MA0701, # <u>22</u> Appendix MA0702 - MA0732, # <u>23</u> Appendix MA0733 - MA0742, # <u>24</u> Appendix MA0743 - MA0750, # <u>25</u> Appendix MA0751 - MA0766, # <u>26</u> Appendix MA0767 - MA0772, # <u>27</u> Appendix MA0773 - MA0780, # <u>28</u> Appendix MA0781 - MA0807, # <u>29</u> Appendix MA0808 - MA0824, # <u>30</u> Appendix MA0825 - MA0831.1, # <u>31</u> Appendix MA0832 - MA0838, # <u>32</u> Appendix MA0839 - MA0844, # <u>33</u> Appendix MA0845 - MA0858, # <u>34</u> Appendix MA0859 - MA0868, # <u>35</u> Appendix MA0869 - MA0877, # <u>36</u> Appendix MA0878 - MA0884, # <u>37</u> Appendix MA0885 - MA0887, # <u>38</u> Appendix MA0888 - MA0891, # <u>39</u> Appendix MA0892 - MA0909, # <u>40</u> Appendix MA0910 - MA0931, # <u>41</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)</p>

REDACTED VERSION of <u>198</u> Opening Brief in Support,, <i>SOITEC/CEA Parties' Opening Brief In Support Of Motion For Summary Judgment: Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)
REDACTED VERSION of <u>197</u> SEALED MOTION for Summary Judgment <i>SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)</i> SEALED MOTION for Summary Judgment <i>SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)</i> <i>SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)
REDACTED VERSION of <u>192</u> Appendix, <i>Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VI of XIX</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>193</u> Appendix, <i>Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VIII of XIX</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>194</u> Appendix, <i>Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume X of XIX</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>195</u> Appendix, <i>Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XVII of XIX</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>196</u> Appendix, <i>Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XIX of XIX</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
APPENDIX re <u>228</u> Claim Construction Answering Brief by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0782_DA0783, # <u>2</u> Appendix DA0784 - DA0785, # <u>3</u> Appendix DA0786, # <u>4</u> Appendix DA0787 - DA0810, # <u>5</u> Appendix DA0811 - DA0834, # <u>6</u> Appendix DA0835 - DA0845, # <u>7</u> Appendix DA0846 - DA0855, # <u>8</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, <u>228</u> Claim Construction Answering Brief <i>Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
APPENDIX re <u>230</u> Claim Construction Answering Brief, <i>Appendix to Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix PA-0001 - PA-0050, # <u>2</u> Appendix PA-0051 - PA-0083, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)

REDACTED VERSION of <u>183</u> Appendix, <i>Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>170</u> Exhibit to a Document, <i>Exhibit A to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>171</u> Exhibit to a Document, <i>Exhibit B to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>172</u> Exhibit to a Document, <i>Exhibit C to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft, Esq. regarding Courtesy CD-ROM copies of: (1) Plaintiffs' Answering Claim Construction Brief and Appendix; and (2) Plaintiffs' Daubert Motion; Plaintiffs' Motions For Partial Summary Judgment; and Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment. (Kraft, Denise) (Entered: 07/12/2010)
NOTICE OF SERVICE of Re-Notice of Deposition of Dr. Peter Moran on behalf of S.O.I.TEC Silicon on Insulator Technologies, S.A., Commissariat a L'Energie Atomique, and SOITEC U.S.A., Inc. by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/13/2010)
Fourth STIPULATION To Amend Scheduling Order re <u>26</u> Scheduling Order,,, by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/15/2010)
ANSWERING BRIEF in Opposition re <u>186</u> MOTION in Limine <i>SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony</i> filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
SEALED APPENDIX re <u>239</u> Answering Brief in Opposition, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Table of Contents, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/19/2010)
SEALED ANSWERING BRIEF in Opposition re <u>213</u> MOTION for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>208</u> MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents</i> filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)

ANSWERING BRIEF in Opposition re <u>202</u> MOTION for Partial Summary Judgment <i>SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement</i> filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>204</u> MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid</i> filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>210</u> MOTION for Partial Summary Judgment <i>SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement</i> filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>212</u> MOTION for Partial Summary Judgment <i>SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art</i> filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
SEALED ANSWERING BRIEF in Opposition re <u>187</u> MOTION for Partial Summary Judgment of <i>Invalidity of the Asserted Aspar Patent Claims Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims - FILED UNDER SEAL</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Reply Brief due date per Local Rules is 7/29/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
APPENDIX re <u>247</u> Answering Brief in Opposition,, <i>Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1156)</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1103 - PA-1109 - FILED UNDER SEAL, # <u>2</u> Exhibit PA-1110 - PA-1118 - FILED UNDER SEAL, # <u>3</u> Exhibit PA-1119 - PA-1130 - FILED UNDER SEAL, # <u>4</u> Exhibit PA-1131 - PA-1143 - FILED UNDER SEAL, # <u>5</u> Exhibit PA-1144 - PA-1156, # <u>6</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
SEALED ANSWERING BRIEF in Opposition re <u>197</u> SEALED MOTION for Summary Judgment <i>SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)</i> SEALED MOTION for Summary Judgment <i>SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)</i> filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
SEALED ANSWERING BRIEF in Opposition re <u>199</u> MOTION for Summary Judgment of <i>Non-Infringement Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Reply Brief due date per Local Rules is 7/29/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
SEALED APPENDIX re <u>250</u> Answering Brief in Opposition, <i>Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1157 - PA-1159 FILED UNDER SEAL, # <u>2</u> Exhibit PA-1160 - PA-1165 FILED UNDER SEAL, # <u>3</u> Exhibit PA-1166 - PA-1168 FILED UNDER SEAL, # <u>4</u> Exhibit PA-1169 - PA-1185 FILED UNDER SEAL, # <u>5</u> Exhibit PA-1186 - PA-1189)(Kraft, Denise) (Entered: 07/19/2010)

<p>APPENDIX re <u>250</u> Answering Brief in Opposition, <i>Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1190 - PA-1191, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)</p>
<p>SEALED ANSWERING BRIEF in Opposition re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010); CORRECTING ENTRY: Docket clerk deleted sealed exhibits 1-4 attached to D.I. 248 due to documents being filed improperly. Counsel is advised that sealed and public documents may not be filed together and to re-file documents using the EXHIBIT TO A DOCUMENT event code indicating that documents are under seal. (lid) (Entered: 07/20/2010)</p>
<p>SEALED APPENDIX re <u>247</u> Answering Brief in Opposition,, <i>Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1143 FILED UNDER SEAL)</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1103 - PA-1109 FILED UNDER SEAL, # <u>2</u> Exhibit PA-1110 - PA-1118 FILED UNDER SEAL, # <u>3</u> Exhibit PA-1119 - PA-1130 FILED UNDER SEAL, # <u>4</u> Exhibit PA-1131 - PA-1143, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 07/20/2010)</p>
<p>NOTICE OF SERVICE of Documents Marked MEMC0782013 - MEMC0782178 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 07/21/2010)</p>
<p>Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Courtesy CD-ROM copies of: (1) Plaintiffs Answering Brief In Opposition To Defendants Motion For Partial Summary Judgment of Invalidity of The Asserted Aspar Claims and Appendix; and (2) Soitecs Brief In Opposition To Defendants Motion For Summary Judgment of Non-Infringement and Appendix. (Kraft, Denise) (Entered: 07/21/2010); SO ORDERED- re <u>238</u> STIPULATION To Amend Scheduling Order. ORDER- Setting Scheduling Order Deadlines (Reply Brief due 7/30/2010.)(REFER TO STIPULATION FOR DETAILS). Signed by Judge Sue L. Robinson on 7/22/2010. (lid) (Entered: 07/22/2010)</p>
<p>REDACTED VERSION of <u>241</u> Answering Brief in Opposition, <i>to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>249</u> Answering Brief in Opposition, <i>to Plaintiffs' Motion for Summary Judgment on the Infringement of U.S. Patent No. 5,834,812</i> by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>253</u> Answering Brief in Opposition, <i>to Plaintiffs' Motion for Partial Summary Judgment that the Aspar Patents Are Not Invalid for Inequitable Conduct</i> by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)</p>

<p>(Document too large to file in pdf format, will file at later date by Express Mail).</p> <p>REDACTED VERSION of <u>240</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0932 - MA0985, # <u>2</u> Appendix MA0986 - MA1039.22, # <u>3</u> Appendix MA1040 - MA1144, # <u>4</u> Appendix MA1145 - MA1200, # <u>5</u> Appendix MA1201 - MA1265, # <u>6</u> Appendix MA1265.1 - MA1338, # <u>7</u> Appendix MA1339 - MA1547, # <u>8</u> Appendix MA1548 - MA1627, # <u>9</u> Appendix MA1628 - MA1693, # <u>10</u> Appendix MA1694 - MA1953, # <u>11</u> Appendix MA1954 - MA2127, # <u>12</u> Appendix MA2128 - MA2206, # <u>13</u> Appendix MA2207 - MA2253, # <u>14</u> Appendix MA2254 - MA2273, # <u>15</u> Appendix MA2274 - MA2333, # <u>16</u> Appendix MA2334 - MA2337, # <u>17</u> Appendix MA2338 - MA2342, # <u>18</u> Appendix MA2343 - MA2346, # <u>19</u> Appendix MA2347 - MA2351, # <u>20</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>SEALED ANSWERING BRIEF in Opposition re <u>213</u> MOTION for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> CORRECTED VERSION OF D.I. 241 filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 8/5/2010. (Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>261</u> Answering Brief in Opposition, to <i>Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> (CORRECTED VERSION OF D.I. 241) by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>250</u> Answering Brief in Opposition, to <i>Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>247</u> Answering Brief in Opposition,, to <i>Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of In validity Of The Asserted Aspar Claims</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>254</u> Appendix,, to <i>Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims</i> (PA-1103 - PA-1143 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)</p>
<p>REDACTED VERSION of <u>251</u> Appendix,, to <i>Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement</i> by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)</p>
<p>SEALED REPLY BRIEF re <u>187</u> MOTION for Partial Summary Judgment of <i>Invalidity of the Asserted Aspar Patent Claims</i> filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/30/2010)</p>
<p>REPLY BRIEF re <u>204</u> MOTION for Partial Summary Judgment <i>Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid</i> Reply Brief in Support of <i>Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid</i> filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)</p>
<p>SEALED APPENDIX re <u>267</u> Reply Brief in Support of <i>MEMC's Motion for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims</i> by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Table of Contents, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/30/2010)</p>

DECLARATION re 268 Reply Brief, Declaration of Marcus T. Hall in Support of Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Exhibit A, # 2 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

SEALED REPLY BRIEF re 199 MOTION for Summary Judgment of Non-Infringement filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Certificate of Service)(Rogowski, Patricia) (Entered: 07/30/2010)

APPENDIX re 268 Reply Brief, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1261) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Exhibit PA-1199 - PA-1204, # 2 Exhibit PA-1205 - PA-1206, # 3 Exhibit PA-1206.1, # 4 Exhibit PA-1231 - PA-1237, # 5 Exhibit PA-1238 - PA-1245, # 6 Exhibit PA-1246 - PA-1257, # 7 Exhibit PA-1258 - PA-1261, # 8 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

SEALED APPENDIX re 271 Reply Brief in Support of MEMC's Motion for Summary Judgment of Non-Infringement by MEMC Electronic Materials Inc.. (Attachments: # 1 Table of Contents, # 2 Certificate of Service)(Rogowski, Patricia) (Entered: 07/30/2010)

SEALED APPENDIX re 272 Appendix,, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1198 and PA-1207 - PA-1230 FILED UNDER SEAL) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Exhibit PA-1192 - PA-1198 (FILED UNDER SEAL), # 2 Exhibit PA-1207 - PA-1217 (FILED UNDER SEAL), # 3 Exhibit PA-1218 - PA-1230 (FILED UNDER SEAL), # 4 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

REPLY BRIEF re 210 MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

REPLY BRIEF re 212 MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # 1 Exhibit A, # 2 Exhibit B, # 3 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

REPLY BRIEF re 186 MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Reply Brief in Support of SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

SEALED REPLY BRIEF re <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) Reply Brief in Support of SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
SEALED REPLY BRIEF re <u>213</u> MOTION for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> Reply Brief in Support of Plaintiffs' Motion for Partial Summary Judgment <i>That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents</i> (FILED UNDER SEAL) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REPLY BRIEF re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
SEALED REPLY BRIEF re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents (FILED UNDER SEAL) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
SEALED REPLY BRIEF re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct (FILED UNDER SEAL) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft, Esq. regarding Courtesy CD-ROM copies of Plaintiffs' Reply to Daubert Motion and Motions for Partial Summary Judgment, and Plaintiffs' Omnibus Appendix to the Replies. (Kraft, Denise) (Entered: 08/02/2010)
REDACTED VERSION of <u>269</u> Appendix, TO REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2453_MA2479, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)

<p>REDACTED VERSION of 273 Appendix REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2352 - MA2361, # <u>3</u> Appendix MA2362 - MA2371, # <u>4</u> Appendix MA2372 - MA2381, # <u>5</u> Appendix MA2382 - MA2391, # <u>6</u> Appendix MA2392 - MA2399, # <u>7</u> Appendix MA2400 - MA2404, # <u>8</u> Appendix MA2405 - MA2422, # <u>9</u> Appendix MA2423 - MA2425, # <u>10</u> Appendix MA2426 - MA2427, # <u>11</u> Appendix MA2428 - MA2430, # <u>12</u> Appendix MA2431 - MA2440, # <u>13</u> Appendix MA2441 - MA2448, # <u>14</u> Appendix MA2449 - MA2452, # <u>15</u> Appendix MA2452.1 - MA2452.9, # <u>16</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)</p>
<p>Letter to The Honorable Sue L. Robinson from Patricia Smink Rogowski regarding CD-ROM copies of (1) MEMC's Claim Construction Briefing, (2) MEMC's Briefs in Support of MEMC's Motion for Summary Judgment, and (3) MEMC's Briefs in Opposition to Soitec's Summary Judgment Motions. (Rogowski, Patricia) (Entered: 08/03/2010)</p>
<p>REDACTED VERSION of 267 Reply Brief IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)</p>
<p>REDACTED VERSION of 271 Reply Brief IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)</p>

Applicants are enclosing Form PTO-1449, along with a copy of each listed reference E149- E681 for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98 and, more particularly, in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following documents. These documents are litigation documents filed by the Parties in *SOITEC v. MEMC* (1:08-cv-00292-SLR) in the U.S. District Court, District of Delaware. This lawsuit involves patents owned by the assignee of record and that disclose subject matter that may be related to that claimed in the above-referenced patent application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other

information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have further calculated a processing fee in the amount of \$180.00 to be due under 37 CFR §1.17(p) in connection with the filing of this Information Disclosure Statement.

Respectfully submitted,

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